

ABSTRACT

Disclosed is a method of forming the dual damascene pattern in the semiconductor device. After forming the trench, a photoresist pattern in which a via hole region is defined is formed by exposure and development processes in a state that a photoresist is thinly coated, in a dual damascene process for first forming the trench than a via hole. Therefore, the present invention can prevent degradation of resolution due to a thickness of a photoresist pattern in a trench region and improve reliability of the entire process by simultaneously smoothly performing an etching process even with a thin photoresist pattern due to a good etching tolerance property.